IR HiRel
An Infineon Technologies Company

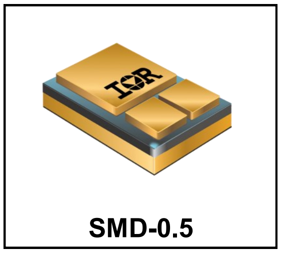
IRHNJ67130
JANSR2N7587U3

RADIATION HARDENED POWER MOSFET SURFACE MOUNT (SMD-0.5)

100V, N-CHANNEL
REF: MIL-PRF-19500/746
R6 TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	I_D	QPL Part Number
IRHNJ67130	100 kRads(Si)	0.042Ω	22A*	JANSR2N7587U3
IRHNJ63130	300 kRads(Si)	0.042Ω	22A*	JANSF2N7587U3


SMD-0.5

Description

IR HiRel R6 technology provides high performance power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm^2). Their combination of very low RDS(on) and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.

Features

- Low $R_{DS(on)}$
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Hermetically Sealed
- Ceramic Package
- Surface Mount
- ESD Rating: Class 1C per MIL-STD-750, Method 1020

Absolute Maximum Ratings

Pre-Irradiation

Symbol	Parameter	Value	Units
I_{D1} @ V_{GS} = 12V, T_C = 25°C	Continuous Drain Current	22*	A
I_{D2} @ V_{GS} = 12V, T_C = 100°C	Continuous Drain Current	19	
I_{DM} @ T_C = 25°C	Pulsed Drain Current ①	88	
P_D @T_C = 25°C	Maximum Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②	73	mJ
I_{AR}	Avalanche Current ①	22	A
E_{AR}	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	3.8	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (for 5s)	
	Weight	1.0 (Typical)	g

* Current is limited by package
For Footnotes, refer to the page 2.

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	100	——	——	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.11	——	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	0.042	Ω	V_{GS} = 12V, I_{D2} = 19A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	——	4.0	V	V_{DS} = V_{GS}, I_D = 1.0mA
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	——	-8.83	——	mV/°C	
gfs	Forward Transconductance	14	——	——	S	V_{DS} = 15V, I_{D2} = 19A ④
I_{DSS}	Zero Gate Voltage Drain Current	——	——	10	µA	V_{DS} = 80V, V_{GS} = 0V
		——	——	25		V_{DS} = 80V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Leakage Forward	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Leakage Reverse	——	——	-100		V_{GS} = -20V
Q_G	Total Gate Charge	——	——	50	nC	I_{D1} = 22A
Q_{GS}	Gate-to-Source Charge	——	——	15		V_{DS} = 50V
Q_{GD}	Gate-to-Drain ('Miller') Charge	——	——	20		V_{GS} = 12V
$t_{d(on)}$	Turn-On Delay Time	——	——	25	ns	V_{DD} = 50V
t_r	Rise Time	——	——	30		I_{D1} = 22A
$t_{d(off)}$	Turn-Off Delay Time	——	——	60		R_G = 7.5Ω
t_f	Fall Time	——	——	30		V_{GS} = 12V
$L_S + L_D$	Total Inductance	——	4.0	——	nH	Measured from center of Drain pad to center of Source pad
C_{iss}	Input Capacitance	——	1730	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	340	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	6.0	——		f = 1.0MHz
R_G	Gate Resistance	——	1.03	——	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	——	——	22*	A	
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	88		
V_{SD}	Diode Forward Voltage	——	——	1.2	V	T_J=25°C, I_S = 22A, V_{GS}=0V④
t_{rr}	Reverse Recovery Time	——	——	350	ns	T_J=25°C, I_F = 22A,V_{DD} ≤ 25V
Q_{rr}	Reverse Recovery Charge	——	——	3.0	µC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

* Current is limited by package

Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	——	1.67	°C/W

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = 25V, starting T_J = 25°C, L = 0.3mH, Peak I_L = 22A, V_{GS} = 12V

③ $I_{SD} \leq$ 22A, di/dt $\leq$ 420A/µs, V_{DD} $\leq$ 100V, $T_J \leq$ 150°C

④ Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

⑤ Total Dose Irradiation with V_{GS} Bias. 12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

⑥ Total Dose Irradiation with V_{DS} Bias. 80 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR Hirel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

Symbol	Parameter	Up to 300 kRads (Si)[1]		Units	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	100	——	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	V	V_{DS} = V_{GS}, I_D = 1.0mA
I_{GSS}	Gate-to-Source Leakage Forward	——	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	——	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	——	10	µA	V_{DS} = 80V, V_{GS} = 0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-3)	——	0.045	Ω	V_{GS} = 12V, I_{D2} = 19A
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (SMD-0.5)	——	0.042	Ω	V_{GS} = 12V, I_{D2} = 19A
V_{SD}	Diode Forward Voltage ④	——	1.2	V	V_{GS} = 0V, I_S = 22A

1. Part numbers IRHNJ67130 (JANSR2N7587U3) and IRHNJ63130 (JANSF2N7587U3)

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

LET $(MeV/(mg/cm^2))$	Energy (MeV)	Range (µm)	VDS (V)					
			@ VGS = 0V	@ VGS = -5V	@ VGS = -10V	@ VGS = -15V	@ VGS = -19V	@ VGS = -20V
39 ± 5%	315 ± 5%	40 ± 5%	100	100	100	100	100	40
61 ± 5%	345 ± 5%	32 ± 7.5%	100	100	100	30	——	——
90 ± 5%	375 ± 7.5%	29 ± 7.5%	100	100	——	——	——	——

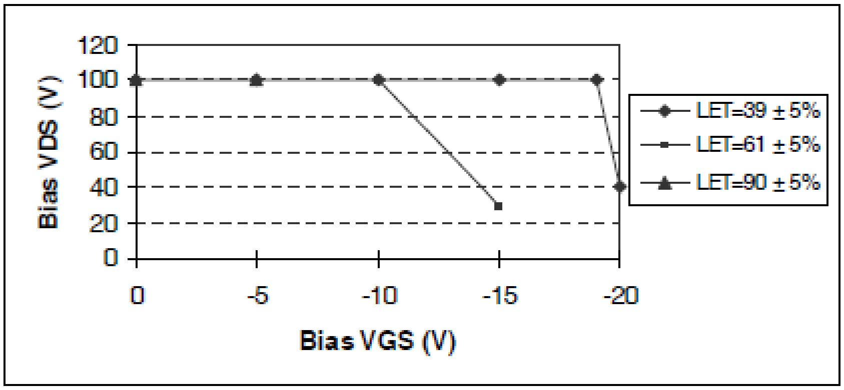


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 2.

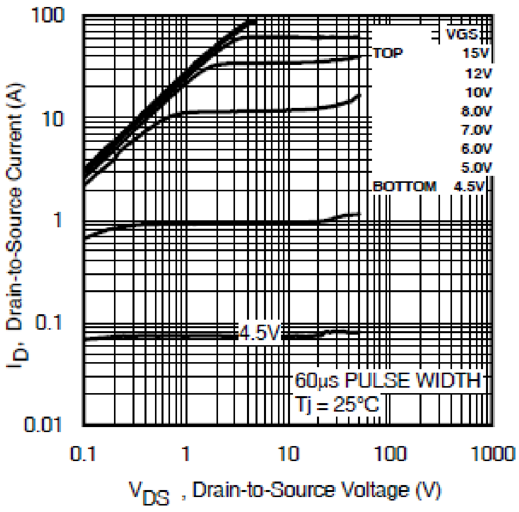


Fig 1. Typical Output Characteristics

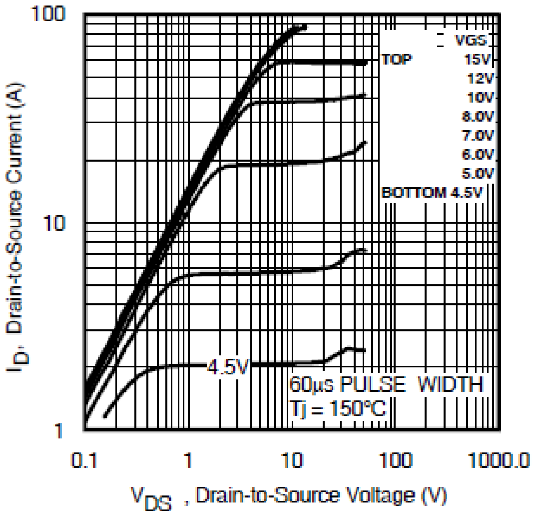


Fig 2. Typical Output Characteristics

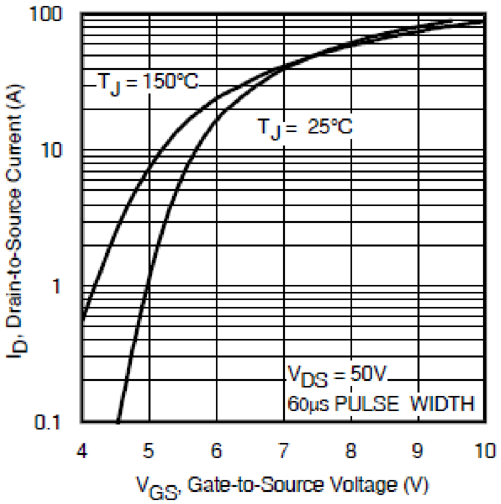


Fig 3. Typical Transfer Characteristics

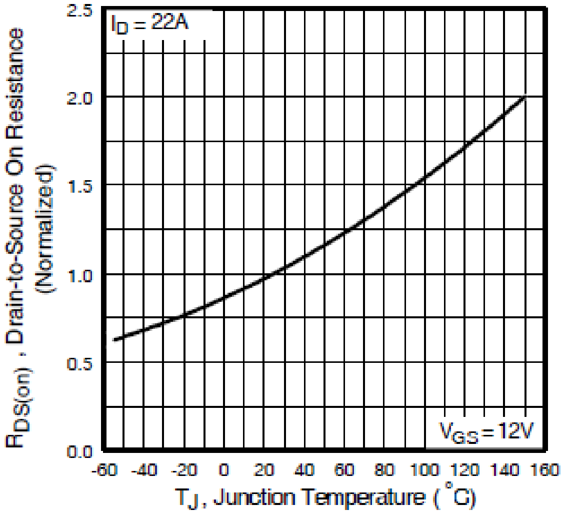


Fig 4. Normalized On-Resistance Vs. Temperature

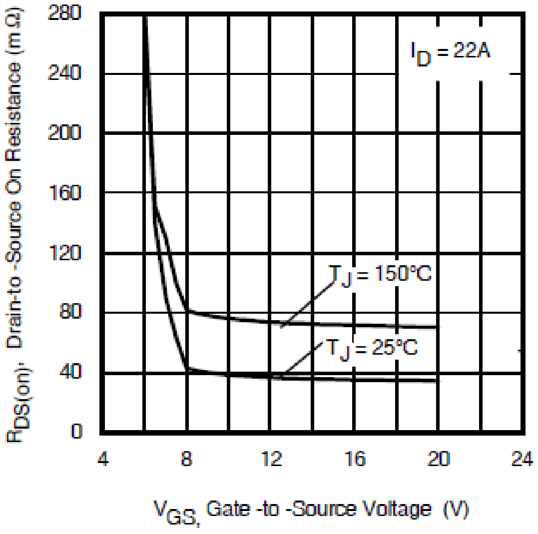


Fig 5. Typical On-Resistance Vs Gate Voltage

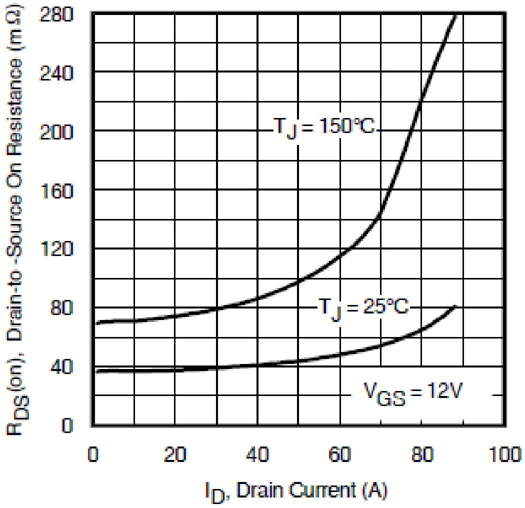


Fig 6. Typical On-Resistance Vs Drain Current

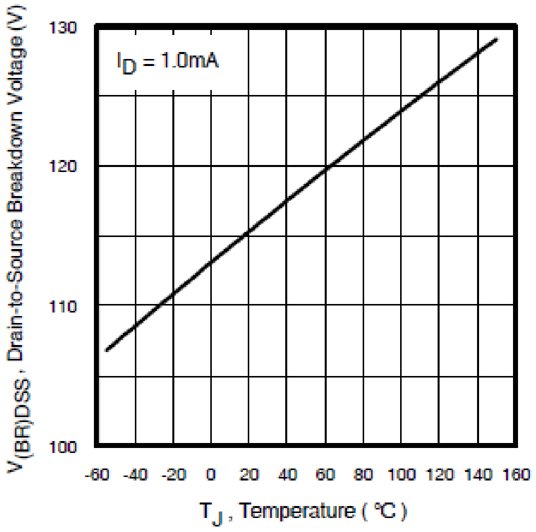


Fig 7. Typical Drain-to-Source Breakdown Voltage Vs Temperature

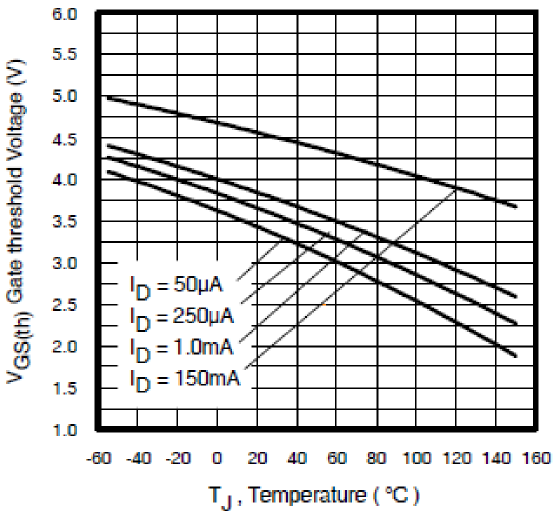


Fig 8. Typical Threshold Voltage Vs Temperature

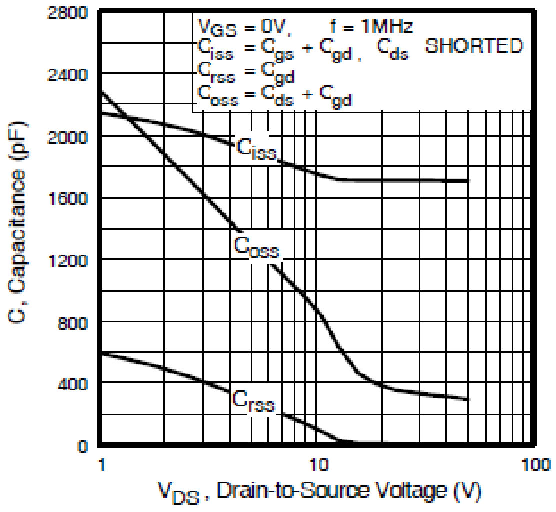


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

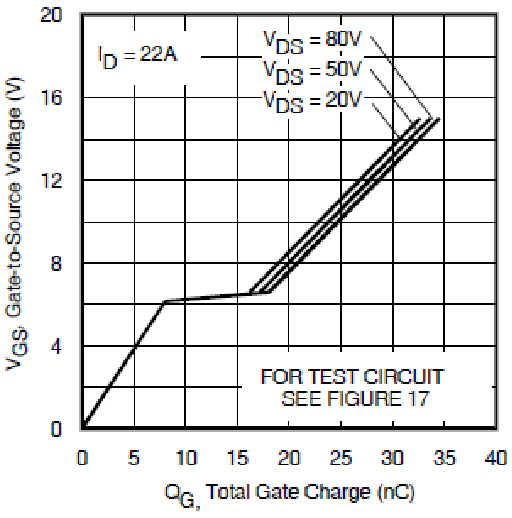


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

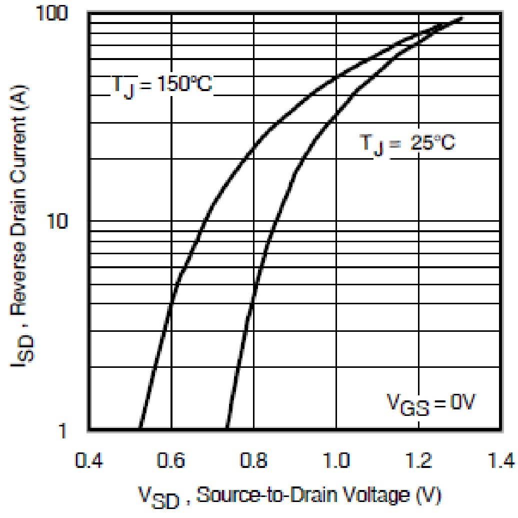


Fig 11. Typical Source-Drain Diode Forward Voltage

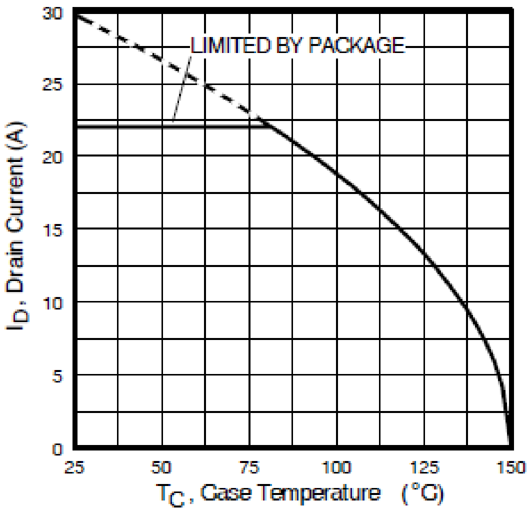


Fig 12. Maximum Drain Current Vs.Case Temperature

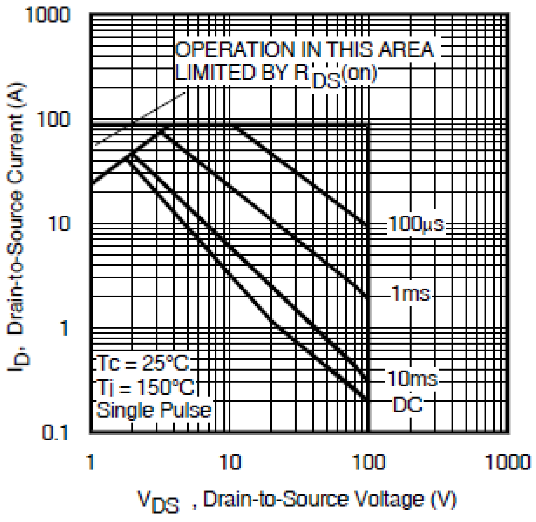


Fig 13. Maximum Safe Operating Area

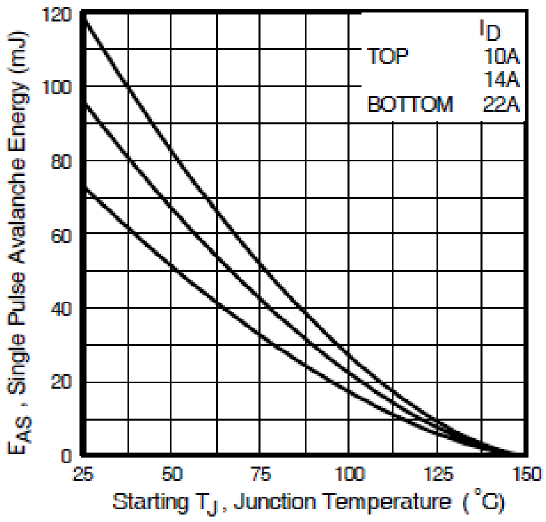


Fig 14. Maximum Avalanche Energy Vs. Drain Current

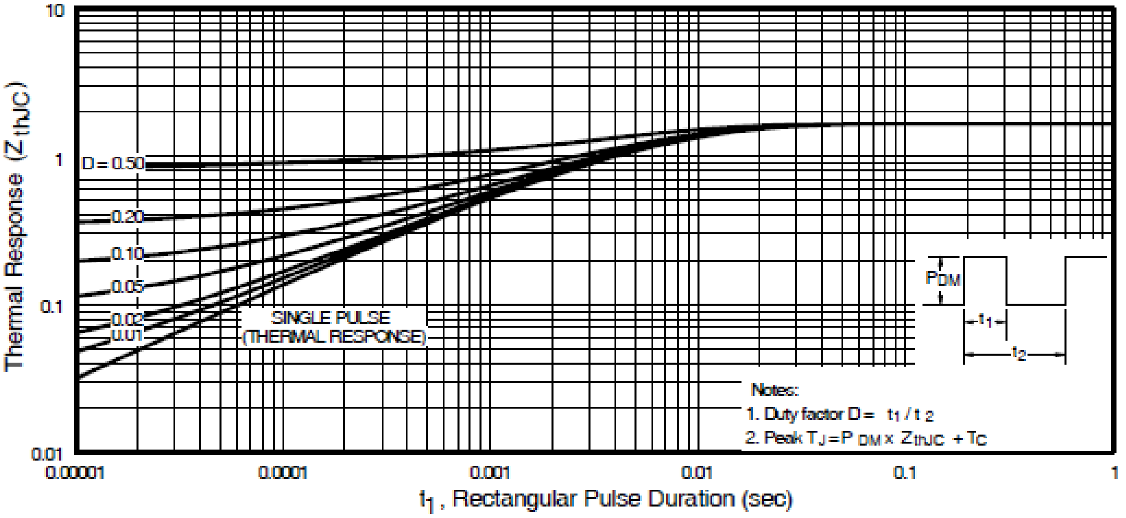


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

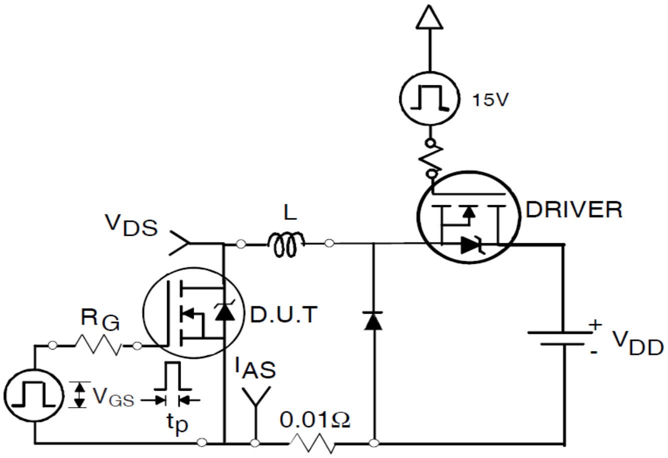


Fig 16a. Unclamped Inductive Test Circuit

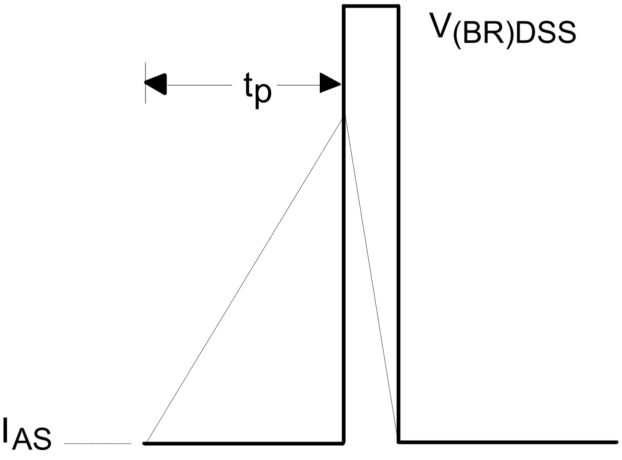


Fig 16b. Unclamped Inductive Waveforms

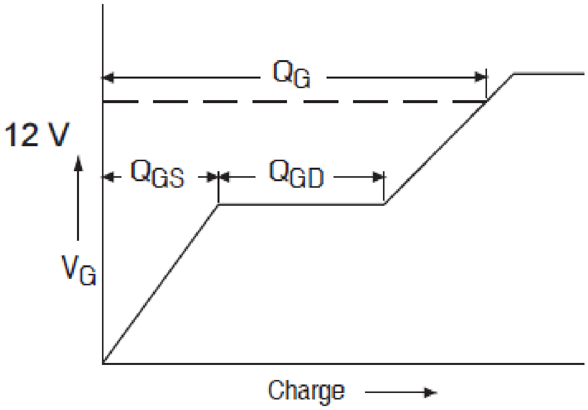


Fig 17a. Gate Charge Waveform

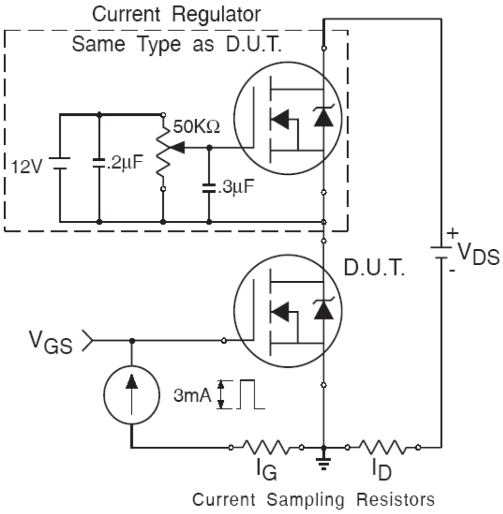


Fig 17b. Gate Charge Test Circuit

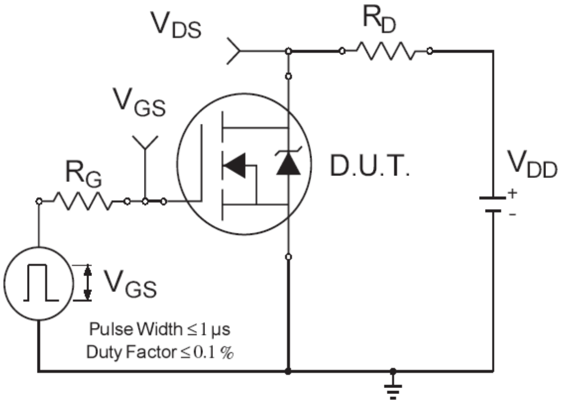


Fig 18a. Switching Time Test Circuit

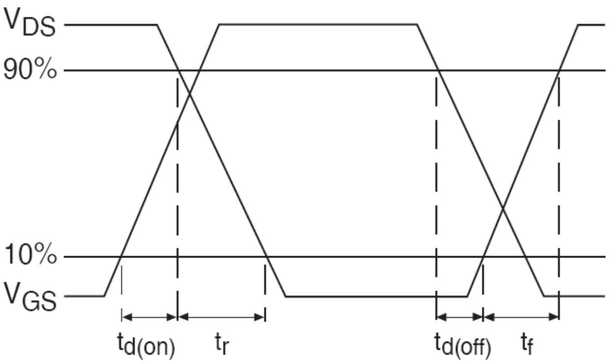
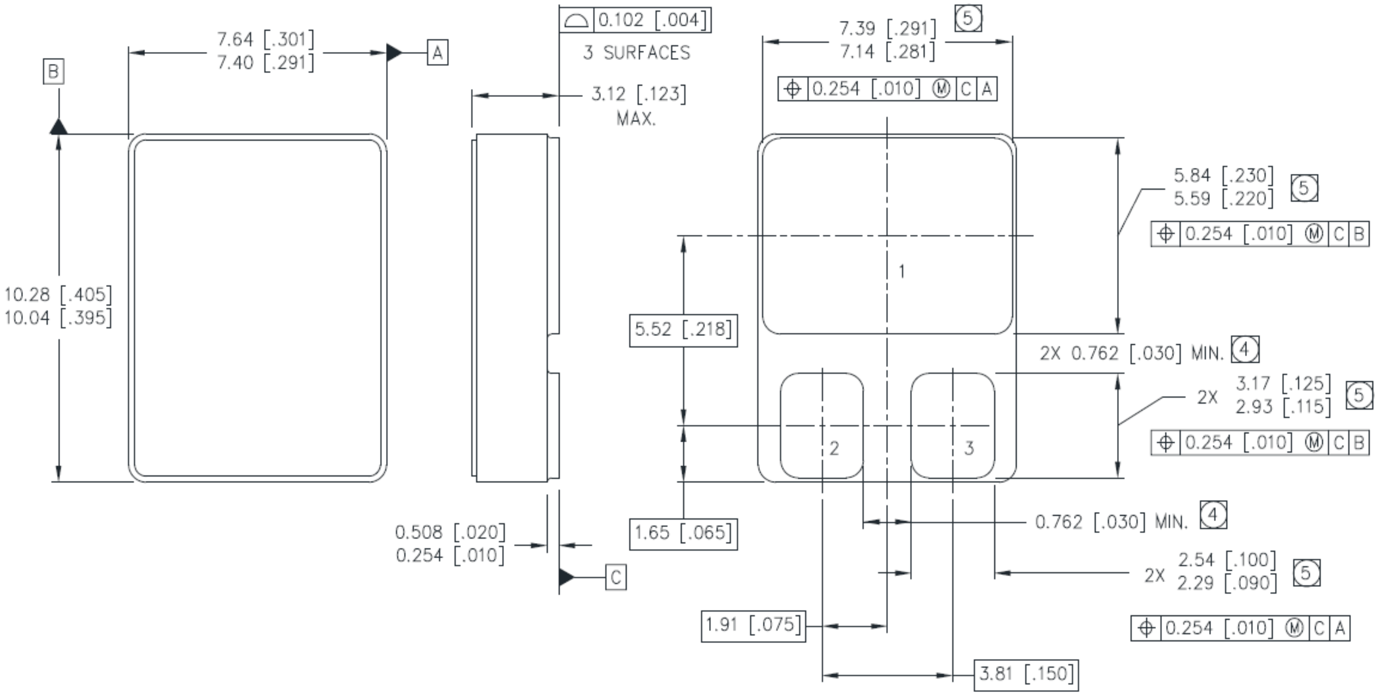


Fig 18b. Switching Time Waveforms

Case Outline and Dimensions — SMD-0.5



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

$\boxed{4}$ DIMENSION INCLUDES METALLIZATION FLASH.

$\boxed{5}$ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

1 = DRAIN
2 = GATE
3 = SOURCE

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